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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO
10/623,861	07/21/2003	Tyler A. Lowrey	ITO.0513C1US (P13341C)	6409
75	590 12/28/20	14	EXAMINER	
Trop, Pruner & Hu, P.C.			SCHILLINGER, LAURA M	
Suite 100 8554 Katy Free	way		ART UNIT	PAPER NUMBER
Houston, TX 77024			2813	

DATE MAILED: 12/28/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

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*	Application No.	Applicant(s)	•			
	10/623,861	LOWREY, TYLER A.				
Office Action Summary	Examiner	Art Unit				
\	Laura M. Schillinger	2813				
The MAILING DATE of this communication appeared for Reply	ppears on the cover sheet w	vith the correspondence address	í			
A SHORTENED STATUTORY PERIOD FOR REP THE MAILING DATE OF THIS COMMUNICATION - Extensions of time may be available under the provisions of 37 CFR 1 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a re - If NO period for reply is specified above, the maximum statutory perio - Failure to reply within the set or extended period for reply will, by statt Any reply received by the Office later than three months after the mail earned patent term adjustment. See 37 CFR 1.704(b).	I. 1.136(a). In no event, however, may a sply within the statutory minimum of th d will apply and will expire SIX (6) MC ate, cause the application to become	a reply be timely filed hirty (30) days will be considered timely. DNTHS from the mailing date of this communi ABANDONED (35 U.S.C. § 133).	ication.			
Status						
1) Responsive to communication(s) filed on 13	December 2004.					
,— «· · · · · · · · · · · · · · · · · · ·	nis action is non-final.					
3) Since this application is in condition for allow						
closed in accordance with the practice under	Ex parte Quayle, 1935 C.	D. 11, 453 O.G. 213.				
Disposition of Claims						
4) ☐ Claim(s) 1-50 is/are pending in the application 4a) Of the above claim(s) 11-30 and 37-50 is 5) ☐ Claim(s) is/are allowed. 6) ☐ Claim(s) 1-10 and 31-36 is/are rejected. 7) ☐ Claim(s) is/are objected to. 8) ☐ Claim(s) are subject to restriction and	/are withdrawn from consi	deration.				
Application Papers						
9) The specification is objected to by the Examination The drawing(s) filed on is/are: a) and a Applicant may not request that any objection to the Replacement drawing sheet(s) including the correction. 11) The oath or declaration is objected to by the	ccepted or b) objected to be drawing(s) be held in abey ection is required if the drawin	ance. See 37 CFR 1.85(a). g(s) is objected to. See 37 CFR 1.1				
Priority under 35 U.S.C. § 119						
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority docume 2. Certified copies of the priority docume 3. Copies of the certified copies of the priority docume application from the International Bure * See the attached detailed Office action for a limit	ints have been received. Ints have been received in Tiority documents have been Peau (PCT Rule 17.2(a)).	Application No In received in this National Stage	e e			
Attachment(s)						
1) Notice of References Cited (PTO-892)		Summary (PTO-413)				
Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/0 Paper No(s)/Mail Date	🗖	o(s)/Mail Date f Informal Patent Application (PTO-152) 	_			

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DETAILED ACTION

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

Claims 1-10 and 34-36 are rejected under 35 U.S.C. 102(e) as being anticipated by Harshfield ('156).

Harshfield teaches the following claimed limitations as cited below:

1 (Previously Presented). A method comprising:

forming a lower electrode (Fig. 18 (106));

covering the lower electrode with a protective layer such that said protective layer is

formed directly over said lower electrode (Fig. 18 (110)), and

forming a phase change material over said lower electrode (Fig.20 (118)- see Col.s 12-13,

lines: 65-5; see also Col.13-14, lines: 60-25).

2 (Original). The method of claim 1 further comprising:

defining a singulated opening (Fig. 19 (114));

forming a cup-shaped phase change material in said opening (Fig.20 (118)); and

forming a thermally insulating material in the cup-shaped phase change material (Fig. 21 : (122)).

- 3 (Original). The method of claim 2 including defining said phase change material using a planarization process (Fig. 22 and Col. 13, lines: 20-40).
- 4 (Original). The method of claim 3 including defining said phase change material using a chemical mechanical planarization technique(Fig. 22 and Col.13, lines:20-40).
- 5 (Original). The method of claim 2 including defining a sidewall spacer in said singulated opening (Fig. 37 (192))
- 6 (Original). The method of claim 5 including defining an electrode in said opening (Fig.21 (118)- annular electrode).
- 7 (Original). The method of claim 6 including using said sidewall spacer to define the cup-shape of said phase change material (Fig. 37 (192)).
- 8 (Original). The method of claim 6 including forming a base layer over a substrate and forming said lower electrode over said base layer (Col. 12, lines: 15-20).
- 9. The method of claim 1 including sequentially forming said lower electrode (106)and then said protective layer (110) (Fig.18).

10 (Original). The method of claim 9 including etching said lower electrode and said protective film using the same mask (Col.12, lines: 50-60).

34 (Previously Presented). The method of claim 1 including forming the protective layer of an insulator (Col.12, lines: 35-45).

35 (Previously Presented). The method of claim 34 including forming the protective layer of a material in the form of silicon nitride (Col.12, lines: 35-45).

36 (Previously Presented). The method of claim 35 including forming the silicon nitride in the form of Si3 N4 (Col.12, lines: 35-45).

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 31-33 are rejected under 35 U.S.C. 103(a) as being unpatentable over Harshfield as applied to claim 1 above, and further in view of Urabe ('302).

Harshfield teaches the limitations of claim 1 and teaches that both the lower electrode and protective layer can be formed by CVD, however fails expressly teach that both layers

are formed in the same deposition chamber as recited by claims 31 and 32. Harshfield also fails to mention any chamber deposition process with regard to without venting back to atmosphere as recited by claim 33.

Urabe ('302) teaches a CVD method for depositing both titanium nitride and silicon nitride in the same chamber (Abs., lines: 1-10 and Fig.3). Furthermore, Urabe does not teach to vent back to atmosphere.

It would have been obvious to one of ordinary skill in the art to modify Harshfield's teachings to include forming both the lower electrode (made of titanium nitride) and the protective layer (made of silicon nitride) in the same chamber as taught by Urabe in order to reduce the number of processing steps which would be required in using two chambers. Moreover, Urabe fails to teach to back vent to atmosphere and therefore the Examiner understands that Urabe's chamber deposition is conducted without venting back to atmosphere.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Laura M. Schillinger whose telephone number is (571) 272-1697. The examiner can normally be reached on M-T, R-F 7:00-5:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl W. Whitehead, Jr. can be reached on (571) 272-1702. The fax phone

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number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

LMS

12/24/04